FORM 1449*	INFORMATION DISCLOSURE STATEMENT	Docket Number: 10873.1944USWO	Application Number: CHIKNOWN 10/598, 095			
	IN AN APPLICATION	Applicant: KITAQKA, et al. 106				
	(Lice coveral cheete if necessary)	Filing Date: Management	Group Art Unit: Indexesses 1792			

		U.S. P	ATENT DOCUME	NTS				
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE		
/F.H./	2004/183090	September, 2004	Kitaoka, et al.					
		FOREIG	N PATENT DOCUM	1ENTS				
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION		
H./	1-116013	May, 1989	Japan			YES Abstract	NO	
.H./	2000-327495	November, 2000		-	ļ			
F.H./	2000-327493	October, 2002	Japan			Abstract		
F.H./	2002-293696	October, 2002	Japan	-				
.n./ .H./	2004-300024	January, 2005	Japan			Abstract		
	l		Japan	D . D .: .	L			
H./		DOCUMENTS (Inc						
F.H./	The Society of Chemical Faginers, Japan, "Kagaku Kogaku Binran", vol. 6, 1999, pgs. 426-427 Kawamura, et al., "Growth of Transparent, Large Size GaN Single Crystal with Low Dislocations using Ca-N Flux System", Jnn. Jappl. Phys., Vol. 42							
/F.H./	Kawamura, et al., "Growth of Transparent, Large Size GaN Single Crystal with Low Dislocations using C Flux System", Jpn. J. Appl. Phys., Vol. 42							

53148

EXAMINER /Felisa Hiteshew/ DATE CONSIDERED 08/12/2008

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.